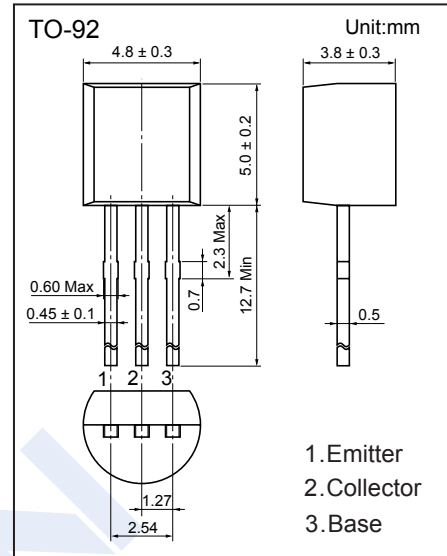


## PNP Transistors

## KTA1266

## ■ Features

- Excellent hFE Linearity
- Low Noise
- Complementary to KTC3198

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CB0}$	-50	V
Collector - Emitter Voltage	$V_{CE0}$	-50	
Emitter - Base Voltage	$V_{EB0}$	-5	
Collector Current - Continuous	$I_C$	-150	mA
Collector Power Dissipation	$P_C$	625	mW
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature range	$T_{stg}$	-55 to 150	

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	$V_{CB0}$	$I_C = -100\mu\text{A}, I_E = 0$	-50			V
Collector- emitter breakdown voltage	$V_{CE0}$	$I_C = -1\text{ mA}, I_B = 0$	-50			
Emitter - base breakdown voltage	$V_{EB0}$	$I_E = -100\mu\text{A}, I_C = 0$	-5			
Collector-base cut-off current	$I_{CB0}$	$V_{CB} = -50\text{V}, I_E = 0$			-0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EB0}$	$V_{EB} = 5\text{V}, I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$			-0.3	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$			-1.1	
DC current gain	$h_{FE(1)}$	$V_{CE} = -6\text{V}, I_C = -2\text{mA}$	70		400	
	$h_{FE(2)}$	$V_{CE} = -6\text{V}, I_C = -150\text{mA}$	25			
Noise figure	NF	$V_{CE} = -6\text{V}, I_C = -0.1\text{mA}, f = 1\text{KHZ}, R_g = 10\text{K}\Omega$			10	dB
Collector output capacitance	$C_{ob}$	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$			7	pF
Transition frequency	$f_t$	$V_{CE} = -10\text{V}, I_C = -1\text{mA}$	80			MHz

■ Classification of  $h_{FE(1)}$ 

Type	KTA1266-O	KTA1266-Y	KTA1266-G
Range	70-140	120-240	200-400

# PNP Transistors

## KTA1266

### Typical Characteristics

